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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Complete if Known	
Application Number	09/945512
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2812
Examiner Name	Booth, Richard

Sheet 1 of 2

Attorney Docket No: 1303.027US1

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Class	Subclass	Filing Date If Appropriate
RB	US-2001/0013621	08/16/2001	Nakazato, K	257	314	12/08/2000
RB	US-2001/0055838	12/27/2001	Walker, A J., et al.	438	129	08/13/2001
RB	US-2002/0028541	03/07/2002	Lee, T H., et al.	438	149	08/13/2001
RB	US-5,691,209	11/25/1997	Liberkowski, J B.	437	7	10/15/1996
RB	US-5,739,544	04/14/1998	Yuki, K., et al.	257	25	12/12/1995
RB	US-6,077,745	06/20/2000	Burns, M S., et al.	438	270	10/29/1997
RB	US-6,306,708	10/23/2001	Peng, N	438	266	02/02/2000
RB	US-6,433,382	08/13/2002	Orlowski, M., et al.	257	315	04/06/1995

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of Cited Document	Class	Subclass	T*

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
RB		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000), pp. 531-537	
RB		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000), pp. 105-113	
RB		FERGUSON, J D., et al., "Atomic layer deposition of Al2O3 and SiO2 on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292	
RB		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta2O5 films", <u>Journal of the Korean Physical Society</u> , (December 2000), pp. 975-979	
RB		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), 4 pages	
RB		KUKLI, KAUPÖ , "Atomic Layer Deposition of Titanium Oxide from TiI4 and H2O2", <u>Chemical Vapor Deposition</u> , (2000), pp. 303-310	
RB		KUKLI, KAUPÖ , et al., "Atomic layer deposition of zirconium oxide from zirconium tetrailoxide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272	
RB		KUKLI, KAUPÖ , et al., "Real-time monitoring in atomic layer deposition of TiO2 from TiI4 and H2O-H2O2", <u>American Chemical Society</u> , (2000), pp. 8122-8128	

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Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with 37 CFR 1.56. Draw line through citation if not in conformance and not considered. (Include copy of this form with final communication to applicant.) Applicant's unique citation designation number (if applicable). Applicant is to place a check mark here if English language Translation is attached.

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		Complete if Known	
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OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. [†]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T [‡]
RB		LEE, J., "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al ₂ O ₃ Gate Dielectric", IEDM, (2000), pp. 645-648	
RB		PARANJPE, AJIT, et al., "Atomic layer deposition of Al ₂ O ₃ for thin film head gap application", Journal of the Electrochemical Society, (September 2001), pp. 465-471	
RB		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", Advanced Materials for Optics and Electronics, (2000), 2 pages	

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